advanced

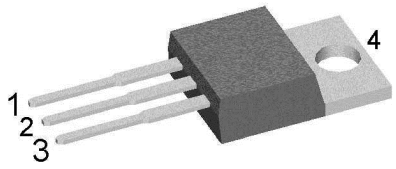
High Efficiency Thyristor

V_{DRM}	=	1200 V
I_{TAV}	=	20 A
V_T	=	1.4 V

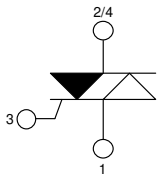
Triode
Single Reverse Conducting Thyristor

Part number

CLA20EF1200PB



Backside: anode



Features / Advantages:

- Thyristor for fast turn-on switching
- Integrated free wheeling diode
- Planar passivated chip
- Long-term stability

Applications:

- Ignition for HD lamps
- Capacity discharge

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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Thyristor

Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
V_{DSM}	*max. non-repetitive forward blocking voltage*		T_{VJ} = 25°C			1300	V
V_{DRM}	*max. repetitive forward blocking voltage*		T_{VJ} = 25°C			1200	V
I_D	*drain current*	V_D = 1200 V	T_{VJ} = 25°C			10	µA
		V_D = 1200 V	T_{VJ} = 125°C			1	mA
V_T	*forward voltage drop*	I_T = 20 A	T_{VJ} = 25°C			1.40	V
	Note:	I_T = 40 A				1.60	V
	reverse voltage drop ~1.2 x VT	I_T = 20 A	T_{VJ} = 125°C			1.40	V
		I_T = 40 A				1.60	V
I_{TAV}	*average forward current*	T_C = 115°C	T_{VJ} = 150°C			20	A
		DC					
V_{T0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 150°C			0.90	V
r_T	*slope resistance* }					25	mΩ
R_{thJC}	*thermal resistance junction to case*					0.65	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.5		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			190	W
I_{TSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			120	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			130	A
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			100	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			110	A
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			72	A²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			70	A²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			50	A²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			50	A²s
C_J	*junction capacitance*	V_R = 400 V f = 1 MHz	T_{VJ} = 25°C		6		pF
P_{GM}	*max. gate power dissipation*	t_P = 30 µs	T_C = 150°C			10	W
		t_P = 300 µs				5	W
P_{GAV}	*average gate power dissipation*					0.5	W
$(di/dt)_{cr}$	*critical rate of rise of current*	T_{VJ} = 150°C; f = 50 Hz	repetitive, I_T = 60 A			500	A/µs
		t_P = 1 µs; di_G/dt = 0.5 A/µs; I_{TSA} = 600 A					
		I_G = 0.07 A; V = ⅔ V_{DRM}	non-repet., I_T = 20 A			1500	A/µs
$(dv/dt)_{cr}$	*critical rate of rise of voltage*	V = ⅔ V_{DRM}	T_{VJ} = 150°C			500	V/µs
		R_{GK} = ∞; method 1 (linear voltage rise)					
V_{GT}	*gate trigger voltage*	V_D = 6 V	T_{VJ} = 25°C			1.3	V
			T_{VJ} = -40°C			1.6	V
I_{GT}	*gate trigger current*	V_D = 6 V	T_{VJ} = 25°C			20	mA
			T_{VJ} = -40°C			35	mA
V_{GD}	*gate non-trigger voltage*	V_D = ⅔ V_{DRM}	T_{VJ} = 150°C			0.2	V
I_{GD}	*gate non-trigger current*					1	mA
I_L	*latching current*	t_p = 10 µs	T_{VJ} = 25°C			30	mA
		I_G = 0.07 A; di_G/dt = 0.5 A/µs					
I_H	*holding current*	V_D = 6 V R_{GK} = ∞	T_{VJ} = 25°C			25	mA
t_{gd}	*gate controlled delay time*	V_D = ½ V_{DRM}	T_{VJ} = 25°C			2	µs
		I_G = 0.07 A; di_G/dt = 0.5 A/µs					
t_q	*turn-off time*	V_R = 0 V; I_T = 20A; V = ⅔ V_{DRM}	T_{VJ} = 125 °C		150		µs
		di/dt = 10 A/µs dv/dt = 20 V/µs t_p = 200 µs					

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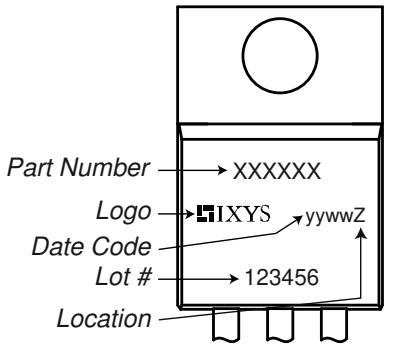
advanced

Package TO-220			Ratings			
Symbol	**Definition**	**Conditions**	**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal			35	A
T_{VJ}	*virtual junction temperature*		-40		150	°C
T_{op}	*operation temperature*		-40		125	°C
T_{stg}	*storage temperature*		-40		150	°C
Weight				2		g
M_D	*mounting torque*		0.4		0.6	Nm
F_C	*mounting force with clip*		20		60	N

Product Marking



Part description

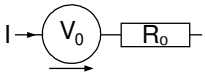
C = Thyristor (SCR)
L = High Efficiency Thyristor
A = (up to 1200V)
20 = Current Rating [A]
EF = Single Reverse Conducting Thyristor
1200 = Reverse Voltage [V]
PB = TO-220AB (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CLA20EF1200PB	CLA20EF1200PB	Tube	50	516273

Similar Part	Package	Voltage class
CLA20EF1200PZ	TO-263AB (D2Pak) (2HV)	1200

Equivalent Circuits for Simulation

** on die level* $T_{VJ} = 150°C$



Thyristor

$V_{0\,max}$	*threshold voltage*	0.9	V
$R_{0\,max}$	*slope resistance **	22	mΩ

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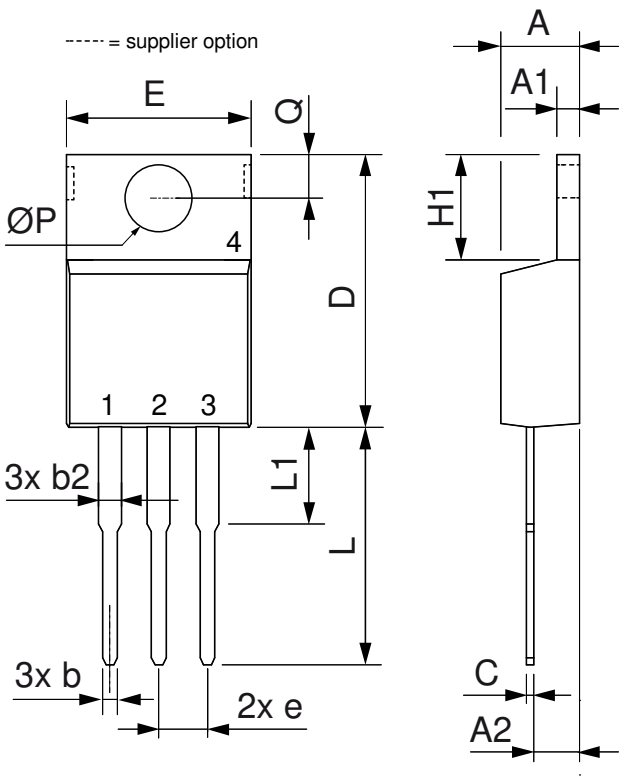
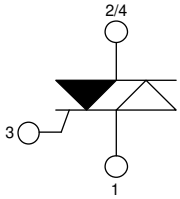
Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	2.54	BSC	0.100	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



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